V_{RRM}	=	6000 V
I_{FAVM}	=	1100 A
I_{FSM}	=	18 kA
V_{F0}	=	1.5 V
r_F	=	0.6 mΩ
V_{DClink}	=	3800 V

Fast Recovery Diode

5SDF 10H6004

Doc. No. 5SYA1109-02 Sep. 01

- **Patented free-floating silicon technology**
- **Low on-state and switching losses**
- **Optimized for use as freewheeling diode in high-voltage GTO converters**
- **Standard press-pack housing, hermetically plasma-welded**
- **Cosmic radiation withstand rating**

Blocking

V_{RRM}	Repetitive peak reverse voltage	6000 V	Half sine wave, t_P = 10 ms, f = 50 Hz	
I_{RRM}	Repetitive peak reverse current	≤ 50 mA	$V_R = V_{RRM}$, T_j = 125°C	
V_{DClink}	Permanent DC voltage for 100 FIT failure rate	3800 V	100% Duty	Ambient cosmic radiation at sea level in open air.
V_{DClink}	Permanent DC voltage for 100 FIT failure rate	V	5% Duty	

Mechanical data (see Fig. 7)

F_m	Mounting force min.	36 kN	
	Mounting force max.	44 kN	
a	Acceleration: Device unclamped Device clamped	 50 m/s² 200 m/s²	
m	Weight	0.83 kg	
D_S	Surface creepage distance	≥ 30 mm	
D_a	Air strike distance	≥ 20 mm	

On-state (see Fig. 2, 3)

I_{FAVM}	Max. average on-state current	1100 A	Half sine wave, T_c = 85°C	
I_{FRMS}	Max. RMS on-state current	1700 A		
I_{FSM}	Max. peak non-repetitive surge current	18 kA	tp = 10 ms	Before surge: $T_c = T_j$ = 125°C
		44 kA	tp = 1 ms	
$\int I^2dt$	Max. surge current integral	$1.62 \cdot 10^6$ A^2s	tp = 10 ms	After surge: $V_R \approx 0$ V
		$0.97 \cdot 10^6$ A^2s	tp = 1 ms	
V_F	Forward voltage drop	≤ 3 V	I_F = 2500 A	T_j = 125°C
V_{F0}	Threshold voltage	1.5 V	Approximation for	
r_F	Slope resistance	0.6 mΩ	I_F = 200…6000 A	

Turn-on (see Fig. 4, 5)

V_{fr}	Peak forward recovery voltage	≤ 95 V	di/dt = 500 A/µs, T_j = 125°C

Turn-off (see Fig. 6)

I_{rr}	Reverse recovery current	≤ 1000 A	di/dt = 300 A/µs, I_F = 3000 A, T_j = 125°C, V_{RM} = 6000 V, C_S = 3µF (GTO snubber circuit)
Q_{rr}	Reverse recovery charge	≤ 4700 µC	
E_{rr}	Turn-off energy	≤ 3.5 J	

Thermal (see Fig. 1)

T_j	Operating junction temperature range	-40...125°C		
T_{stg}	Storage temperature range	-40...125°C		
R_{thJC}	Thermal resistance junction to case	≤ 24 K/kW	Anode side cooled	F_m = 36… 44 kN
		≤ 24 K/kW	Cathode side cooled	
		≤ 12 K/kW	Double side cooled	
R_{thCH}	Thermal resistance case to heatsink	≤ 6 K/kW	Single side cooled	
		≤ 3 K/kW	Double side cooled	

Analytical function for transient thermal impedance.

$$Z_{thJC}(t) = \sum_{i=1}^{n} R_i(1 - e^{-t/\tau_i})$$

i	1	2	3	4
R_i(K/kW)	11.83	2.00	1.84	0.71
τ_i(s)	0.47	0.091	0.01	0.0047
F_m = 36… 44 kN Double side cooled				

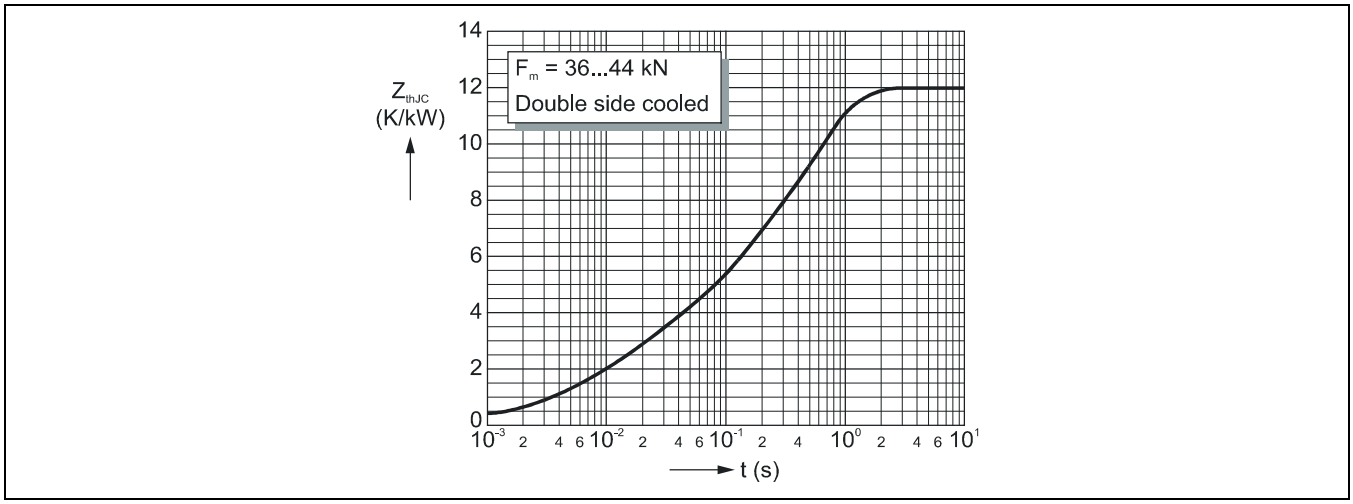

Fig. 1 Transient thermal impedance (junction-to-case) vs. time in analytical and graphical form (max. values).

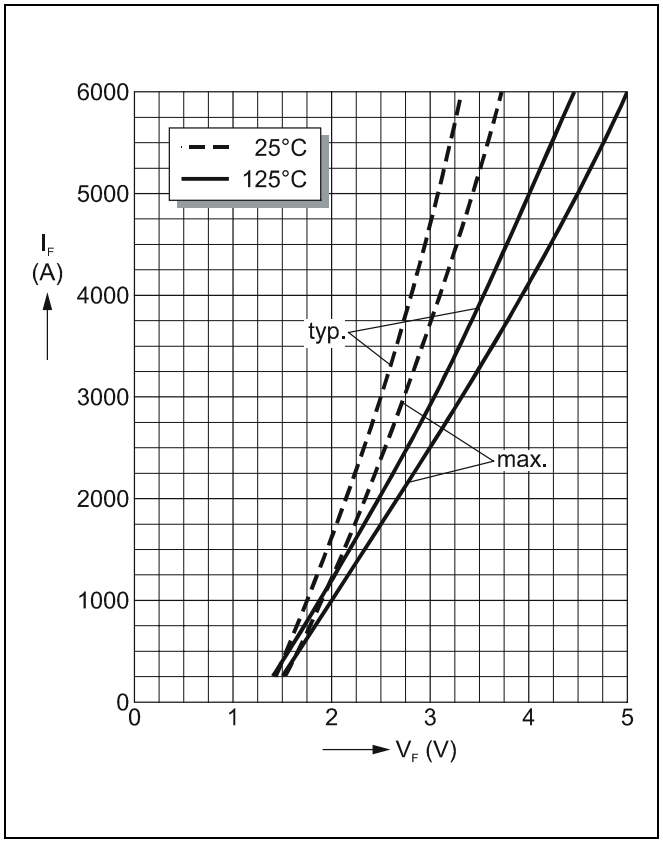

Fig. 2 Forward current vs. forward voltage (typ. and max. values) and linear approximation of max. curve at 125°C.

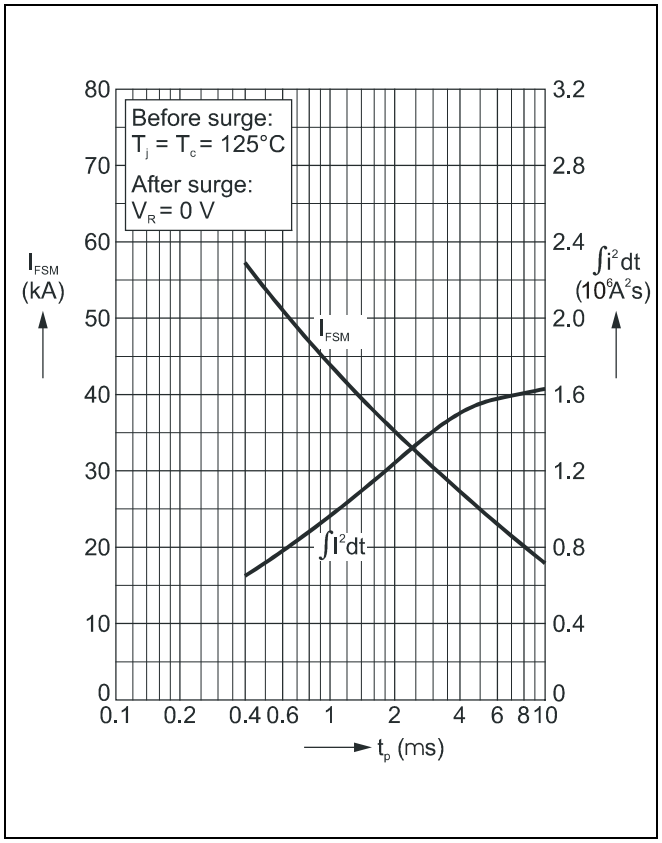

Fig. 3 Surge current and fusing integral vs. pulse width (max. values) for non-repetitive, half-sinusoidal surge current pulses.

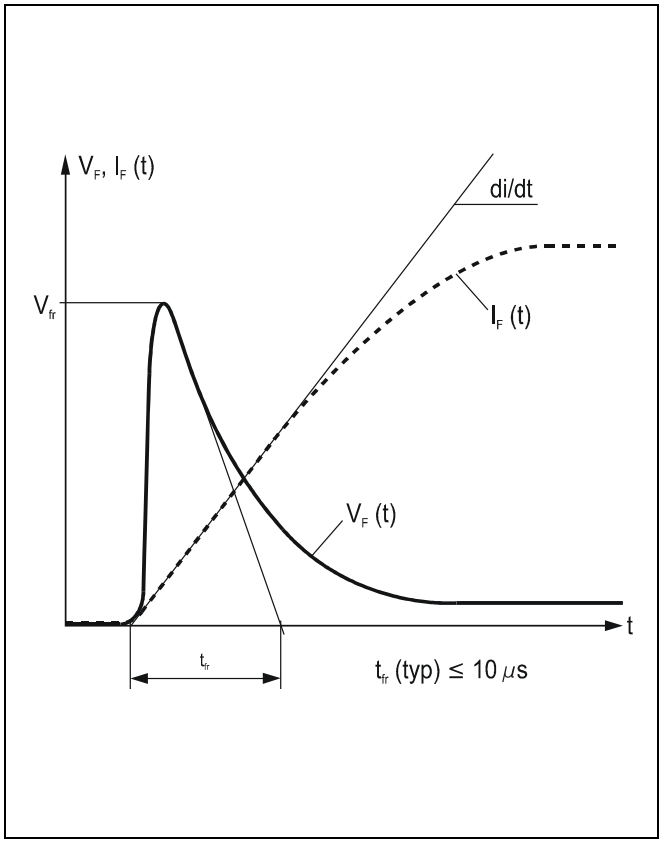

Fig. 4 Typical forward voltage waveform when the diode is turned on with a high di/dt.

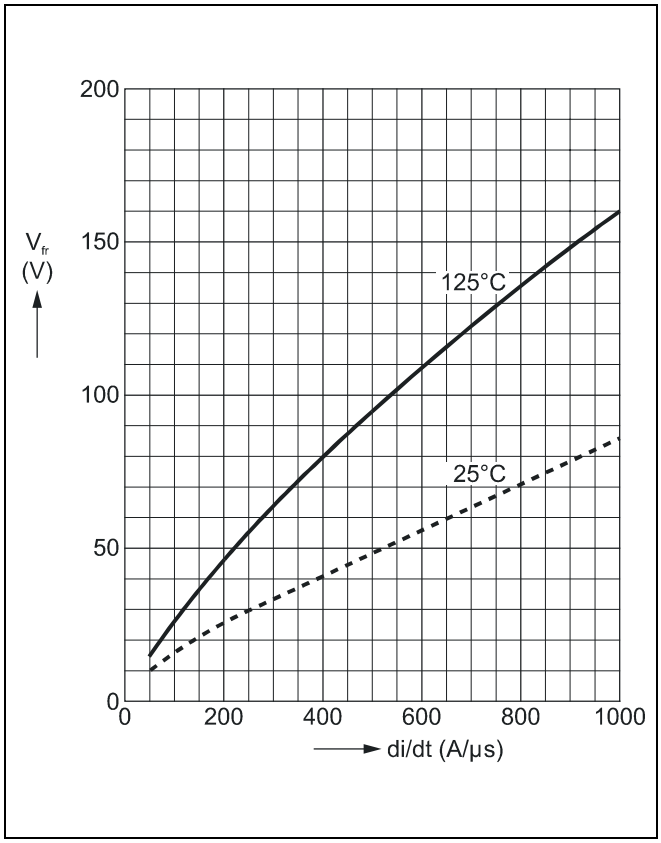

Fig. 5 Forward recovery voltage vs. turn-on di/dt (max. values).

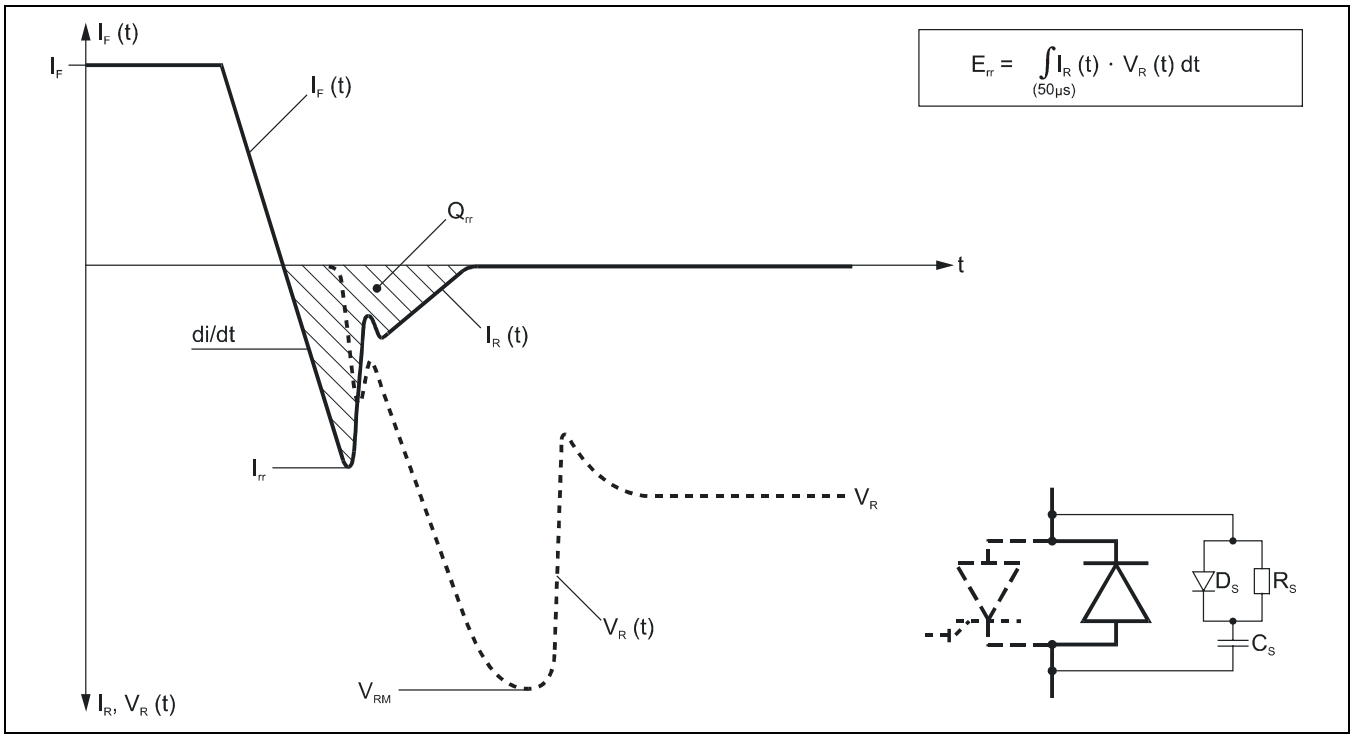

Fig. 6 Typical current and voltage waveforms at turn-off when the diode is connected to an RCD snubber, as often used in GTO circuits.

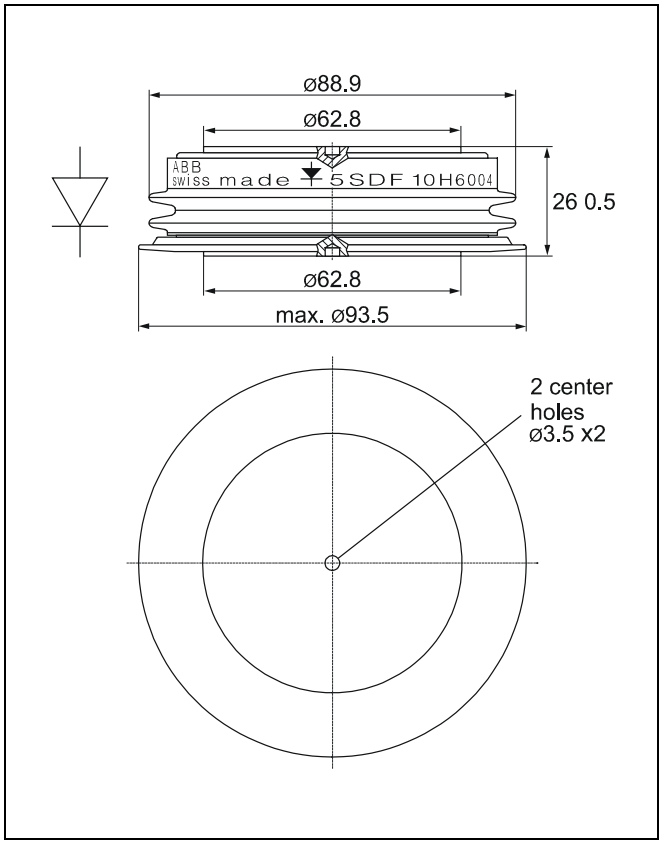

Fig. 7 Outline drawing. All dimensions are in millimeters and represent nominal values unless stated otherwise.

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